

**IGBT-Wechselrichter/IGBT-inverter**

**Höchstzulässige Werte/maximum rated values**

Kollektor-Emitter-Sperrspannung collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{CES}$	1200	V
Kollektor-Dauergleichstrom DC-collector current	$T_C = 80^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}$	$I_{C\ nom}$ $I_C$	150 200	A A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	$t_P = 1\ \text{ms}, T_C = 80^{\circ}\text{C}$	$I_{CRM}$	300	A
Gesamt-Verlustleistung total power dissipation	$T_C = 25^{\circ}\text{C}$	$P_{tot}$	700	W
Gate-Emitter-Spitzenspannung gate-emitter peak voltage		$V_{GES}$	+/-20	V

**Charakteristische Werte/characteristic values**

			min.	typ.	max.	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	$I_C = 150\ \text{A}, V_{GE} = 15\ \text{V}, T_{vj} = 25^{\circ}\text{C}$ $I_C = 150\ \text{A}, V_{GE} = 15\ \text{V}, T_{vj} = 125^{\circ}\text{C}$	$V_{CE\ sat}$		1,70 2,00	2,15	V V
Gate-Schwellenspannung gate threshold voltage	$I_C = 6,00\ \text{mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$	$V_{GEth}$	5,0	5,8	6,5	V
Gateladung gate charge	$V_{GE} = -15\ \text{V} \dots +15\ \text{V}$	$Q_G$		1,40		$\mu\text{C}$
Interner Gatewiderstand internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$	$R_{Gint}$		5,0		$\Omega$
Eingangskapazität input capacitance	$f = 1\ \text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\ \text{V}, V_{GE} = 0\ \text{V}$	$C_{ies}$		10,5		nF
Rückwirkungskapazität reverse transfer capacitance	$f = 1\ \text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\ \text{V}, V_{GE} = 0\ \text{V}$	$C_{res}$		0,40		nF
Kollektor-Emitter Reststrom collector-emitter cut-off current	$V_{CE} = 1200\ \text{V}, V_{GE} = 0\ \text{V}, T_{vj} = 25^{\circ}\text{C}$	$I_{CES}$			5,0	mA
Gate-Emitter Reststrom gate-emitter leakage current	$V_{CE} = 0\ \text{V}, V_{GE} = 20\ \text{V}, T_{vj} = 25^{\circ}\text{C}$	$I_{GES}$			400	nA
Einschaltverzögerungszeit (ind. Last) turn-on delay time (inductive load)	$I_C = 150\ \text{A}, V_{CE} = 600\ \text{V}$ $V_{GE} = \pm 15\ \text{V}, R_{Gon} = 2,4\ \Omega, T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\ \text{V}, R_{Gon} = 2,4\ \Omega, T_{vj} = 125^{\circ}\text{C}$	$t_{d\ on}$		0,26 0,29		$\mu\text{s}$ $\mu\text{s}$
Anstiegszeit (induktive Last) rise time (inductive load)	$I_C = 150\ \text{A}, V_{CE} = 600\ \text{V}$ $V_{GE} = \pm 15\ \text{V}, R_{Gon} = 2,4\ \Omega, T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\ \text{V}, R_{Gon} = 2,4\ \Omega, T_{vj} = 125^{\circ}\text{C}$	$t_r$		0,03 0,05		$\mu\text{s}$ $\mu\text{s}$
Abschaltverzögerungszeit (ind. Last) turn-off delay time (inductive load)	$I_C = 150\ \text{A}, V_{CE} = 600\ \text{V}$ $V_{GE} = \pm 15\ \text{V}, R_{Goff} = 2,4\ \Omega, T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\ \text{V}, R_{Goff} = 2,4\ \Omega, T_{vj} = 125^{\circ}\text{C}$	$t_{d\ off}$		0,42 0,52		$\mu\text{s}$ $\mu\text{s}$
Fallzeit (induktive Last) fall time (inductive load)	$I_C = 150\ \text{A}, V_{CE} = 600\ \text{V}$ $V_{GE} = \pm 15\ \text{V}, R_{Goff} = 2,4\ \Omega, T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\ \text{V}, R_{Goff} = 2,4\ \Omega, T_{vj} = 125^{\circ}\text{C}$	$t_f$		0,07 0,09		$\mu\text{s}$ $\mu\text{s}$
Einschaltverlustenergie pro Puls turn-on energy loss per pulse	$I_C = 150\ \text{A}, V_{CE} = 600\ \text{V}, L_S = 70\ \text{nH}$ $V_{GE} = \pm 15\ \text{V}, R_{Gon} = 2,4\ \Omega, T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\ \text{V}, R_{Gon} = 2,4\ \Omega, T_{vj} = 125^{\circ}\text{C}$	$E_{on}$		16,0		mJ mJ
Abschaltverlustenergie pro Puls turn-off energy loss per pulse	$I_C = 150\ \text{A}, V_{CE} = 600\ \text{V}, L_S = 70\ \text{nH}$ $V_{GE} = \pm 15\ \text{V}, R_{Goff} = 2,4\ \Omega, T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\ \text{V}, R_{Goff} = 2,4\ \Omega, T_{vj} = 125^{\circ}\text{C}$	$E_{off}$		17,0		mJ mJ
Kurzschlußverhalten SC data	$t_P \leq 10\ \mu\text{s}, V_{GE} \leq 15\ \text{V}$ $T_{vj} \leq 125^{\circ}\text{C}, V_{CC} = 900\ \text{V}, V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	$I_{SC}$		600		A
Innerer Wärmewiderstand thermal resistance, junction to case	pro IGBT per IGBT	$R_{thJC}$			0,18	K/W

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**Diode-Wechselrichter/diode-inverter**  
**Höchstzulässige Werte/maximum rated values**

Periodische Spitzensperrspannung repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{RRM}$	1200	V
Dauergleichstrom DC forward current		$I_F$	150	A
Periodischer Spitzenstrom repetitive peak forward current	$t_p = 1 \text{ ms}$	$I_{FRM}$	300	A
Grenzlastintegral $I^2t$ - value	$V_R = 0 \text{ V}, t_p = 10 \text{ ms}, T_{vj} = 125^{\circ}\text{C}$	$I^2t$	4550	$\text{A}^2\text{s}$

**Charakteristische Werte/characteristic values**

			min.	typ.	max.	
Durchlassspannung forward voltage	$I_F = 150 \text{ A}, V_{GE} = 0 \text{ V}, T_{vj} = 25^{\circ}\text{C}$ $I_F = 150 \text{ A}, V_{GE} = 0 \text{ V}, T_{vj} = 125^{\circ}\text{C}$	$V_F$		1,65 1,65	2,15	V V
Rückstromspitze peak reverse recovery current	$I_F = 150 \text{ A}, -di_F/dt = 4000 \text{ A}/\mu\text{s}$ $V_R = 600 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 25^{\circ}\text{C}$ $V_R = 600 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 125^{\circ}\text{C}$	$I_{RM}$		190 210		A A
Sperrverzögerungsladung recovered charge	$I_F = 150 \text{ A}, -di_F/dt = 4000 \text{ A}/\mu\text{s}$ $V_R = 600 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 25^{\circ}\text{C}$ $V_R = 600 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 125^{\circ}\text{C}$	$Q_r$		17,0 30,0		$\mu\text{C}$ $\mu\text{C}$
Abschaltenergie pro Puls reverse recovery energy	$I_F = 150 \text{ A}, -di_F/dt = 4000 \text{ A}/\mu\text{s}$ $V_R = 600 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 25^{\circ}\text{C}$ $V_R = 600 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 125^{\circ}\text{C}$	$E_{rec}$		7,00 13,0		mJ mJ
Innerer Wärmewiderstand thermal resistance, junction to case	pro Diode per diode	$R_{thJC}$			0,34	K/W

**NTC-Widerstand/NTC-thermistor**

**Charakteristische Werte/characteristic values**

			min.	typ.	max.	
Nennwiderstand rated resistance	$T_C = 25^{\circ}\text{C}$	$R_{25}$		5,00		k $\Omega$
Abweichung von $R_{100}$ deviation of $R_{100}$	$T_C = 100^{\circ}\text{C}, R_{100} = 493 \Omega$	$\Delta R/R$	-5		5	%
Verlustleistung power dissipation	$T_C = 25^{\circ}\text{C}$	$P_{25}$			20,0	mW
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298, 15K))]$	$B_{25/50}$		3375		K

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**Modul/module**

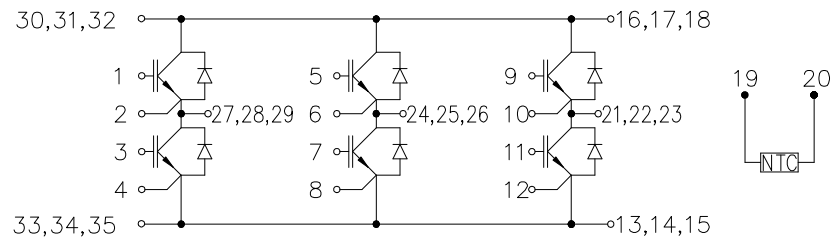
Isolations-Prüfspannung insulation test voltage	RMS, f = 50 Hz, t = 1 min	V <sub>ISO</sub>	2,5		kV
Material für innere Isolation material for internal insulation			Al2O3		
Kriechstrecke creepage distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		10,0		mm
Luftstrecke clearance distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		7,50		mm
Vergleichszahl der Kriechwegbildung comparative tracking index		CTI	> 225		
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	pro Modul / per module $\lambda_{\text{Paste}} = 1 \text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1 \text{ W}/(\text{m}\cdot\text{K})$	R <sub>thCH</sub>		min. 0,009	typ. max. K/W
Modulinduktivität stray inductance module		L <sub>sCE</sub>	21		nH
Modulleitungswiderstand, Anschlüsse - Chip module lead resistance, terminals - chip	T <sub>C</sub> = 25°C, pro Zweig / per arm	R <sub>CC'-EE'</sub>	1,80		mΩ
Höchstzulässige Sperrschichttemperatur maximum junction temperature		T <sub>vj max</sub>			150 °C
Temperatur im Schaltbetrieb temperature under switching conditions		T <sub>vj op</sub>	-40		125 °C
Lagertemperatur storage temperature		T <sub>stg</sub>	-40		125 °C
Anzugsdrehmoment f. mech. Befestigung mounting torque	Schraube / screw M5	M	3,00	-	6,00 Nm
Gewicht weight		G		300	g

**Mit dieser technischen Information werden Halbleiterbauelemente spezifiziert, jedoch keine Eigenschaften zugesichert. Sie gilt in Verbindung mit den zugehörigen technischen Erläuterungen.**

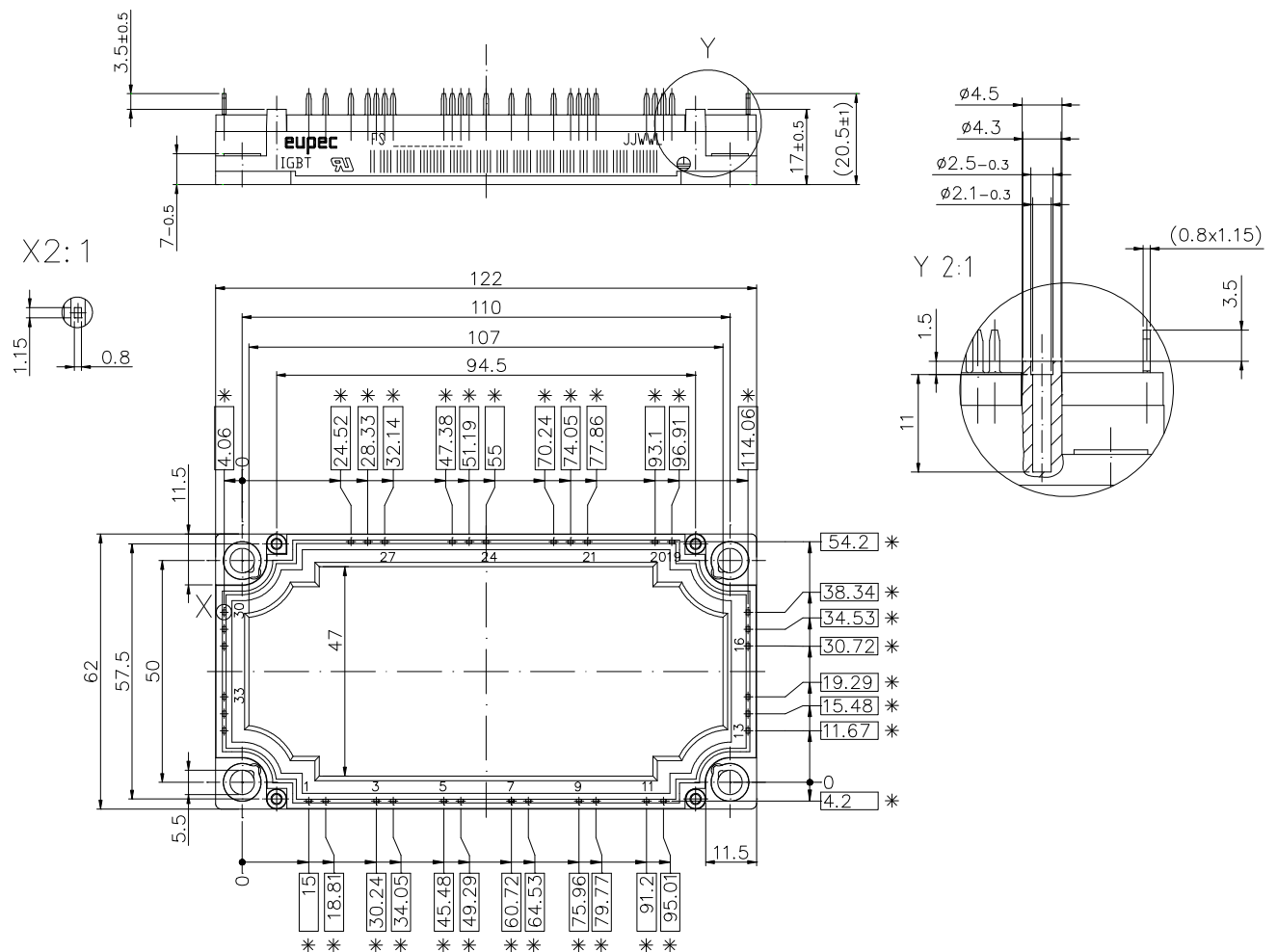
**This technical information specifies semiconductor devices but guarantees no characteristics. It is valid with the appropriate technical explanations.**

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## Schaltplan/circuit diagram



## Gehäuseabmessungen/package outlines



\* = alle Maße mit einer Toleranz von  $\pm 0.5$

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